

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-8 (Canceled)

Claim 9 (New): A power semiconductor element, comprising:

an emitter region; and

a stop zone in front of said emitter region, the stop zone and said emitter region having mutually opposite conductivities, the stop zone including sulfur atoms with at least one energy level within the band gap of the semiconductor and at least 200 meV away from both a conduction band and a valence band of the semiconductor, the stop zone having a doping profile of sulfur atoms such that the stop zone is only partially electrically active in the on-state and fully electrically active in the off-state for carriers emitted by the emitter region.

Claim 10 (New): A power semiconductor element, comprising:

an emitter region; and

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a stop zone in front of said emitter region, the stop zone and said emitter region having mutually opposite conductivities, the stop zone including selenium atoms with at least one energy level within the band gap of the semiconductor and at least 200 meV away from both a conduction band and a valence band of the semiconductor, the stop zone having a doping profile of selenium atoms such that the stop zone is only partially electrically active in the on-state and fully electrically active in the off-state for carriers emitted by the emitter region.